

A New Monolithic Dielectric Resonator Metasurface Design for High Quality- Factor Fano Resonances

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Fano resonances of dielectric resonator metasurfaces

Fano resonances:

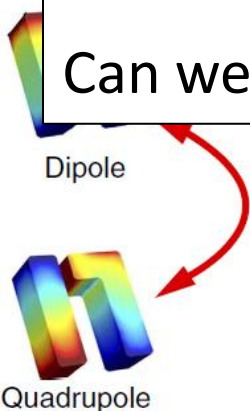
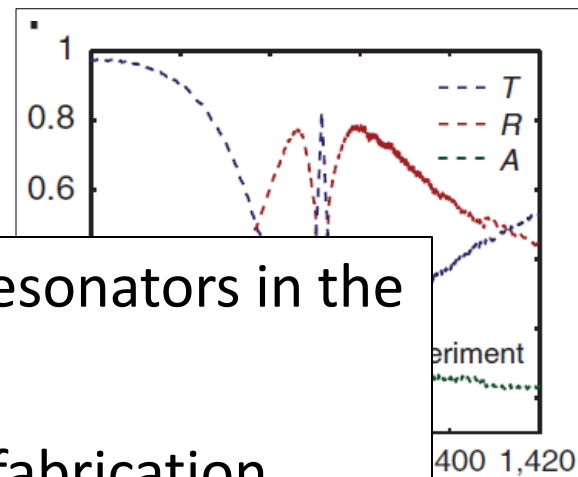
- Interference of bright and dark excitations

Techn

- DR Fano designs to-date rely on multiple resonators in the unit cell

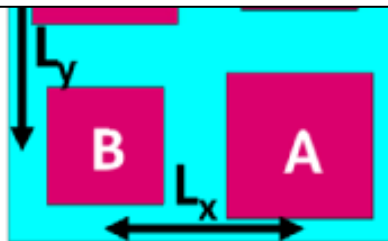
Near field coupling extremely sensitive to fabrication errors

Can we find a one-resonator design??



$Q \sim 130$ at 4 μm

Wu, et al.
Nature Comm. 5, 3892, 2014



$Q \sim 110$ at 1.1 μm

Wang, et al.
OMEX 5, 668, 2015



$Q \sim 500$ at 1.37 μm

Yang, et al.
Nature Comm. 5, 5753, 2014



A new, monolithic, Fano resonator design

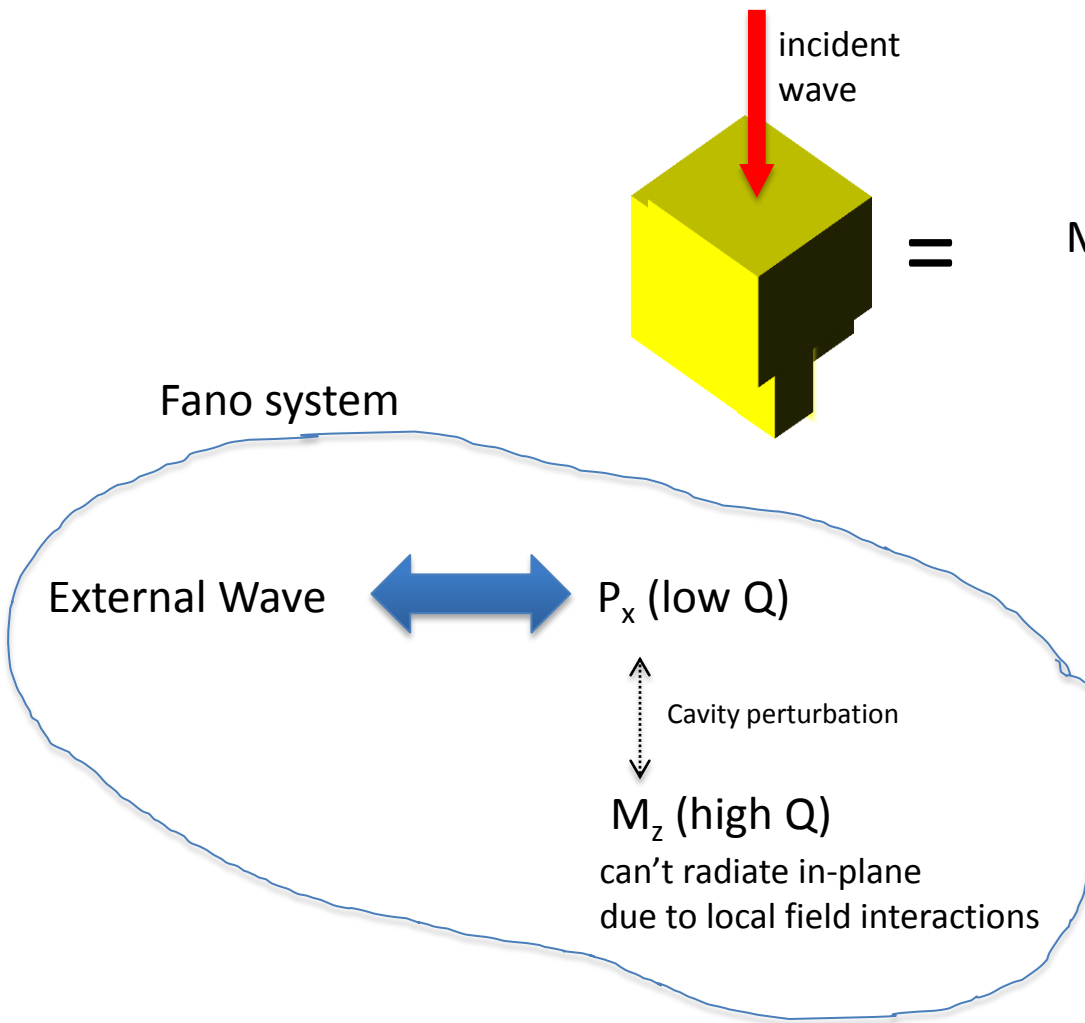


Outline

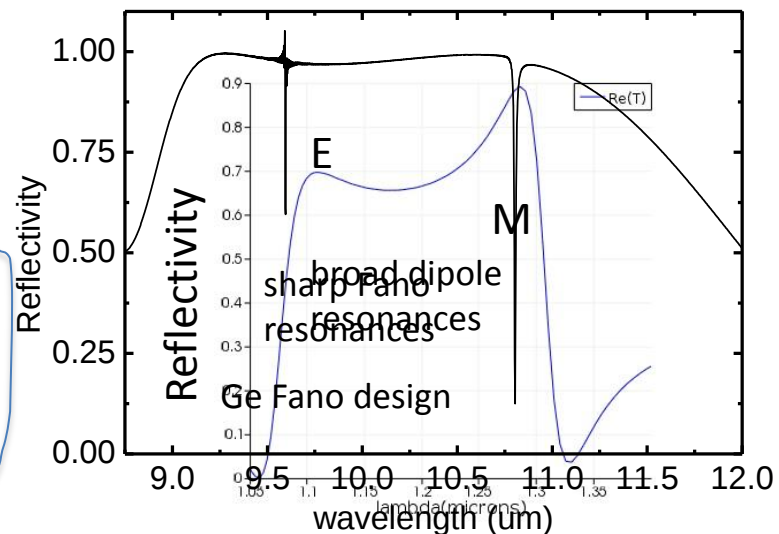
- Hi-Q monolithic design
- Theoretical underpinnings
- Experimental demonstrations:
 - SOI: measured Q-factor of ≈ 350 at 990 nm
 - GaAs: Q-factor of ≈ 600 at 975 nm



Fano resonator design: operating principles

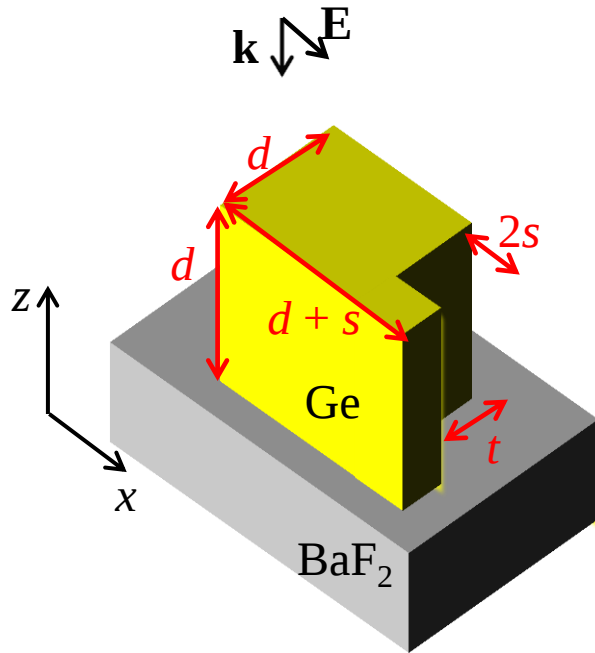


weakly coupled
dipole
modes

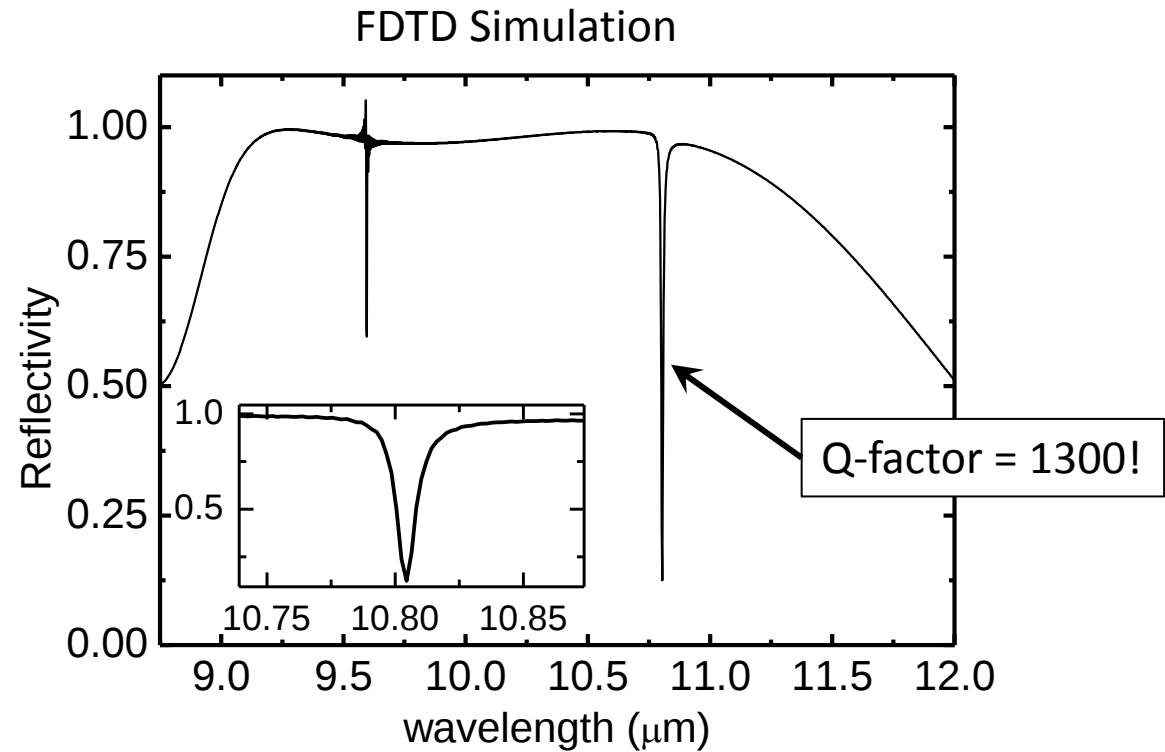




Ge-based Fano design



$$\begin{aligned}d &= 2.53 \mu\text{m} \\s &= d / 5 \\a &= b = 4.2 \mu\text{m} \\t &= 1.5 \mu\text{m}\end{aligned}$$



Design is scalable from NIR through RF!

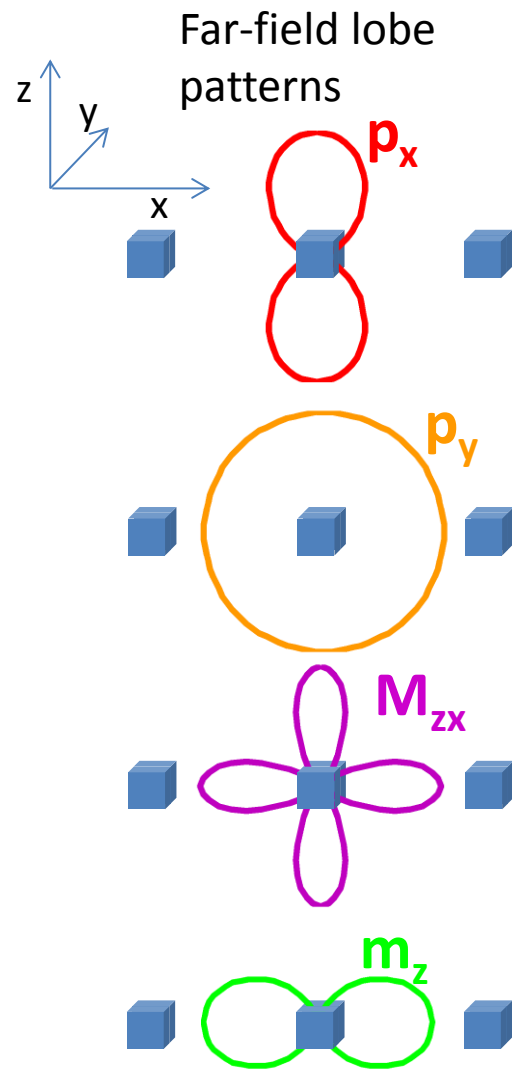
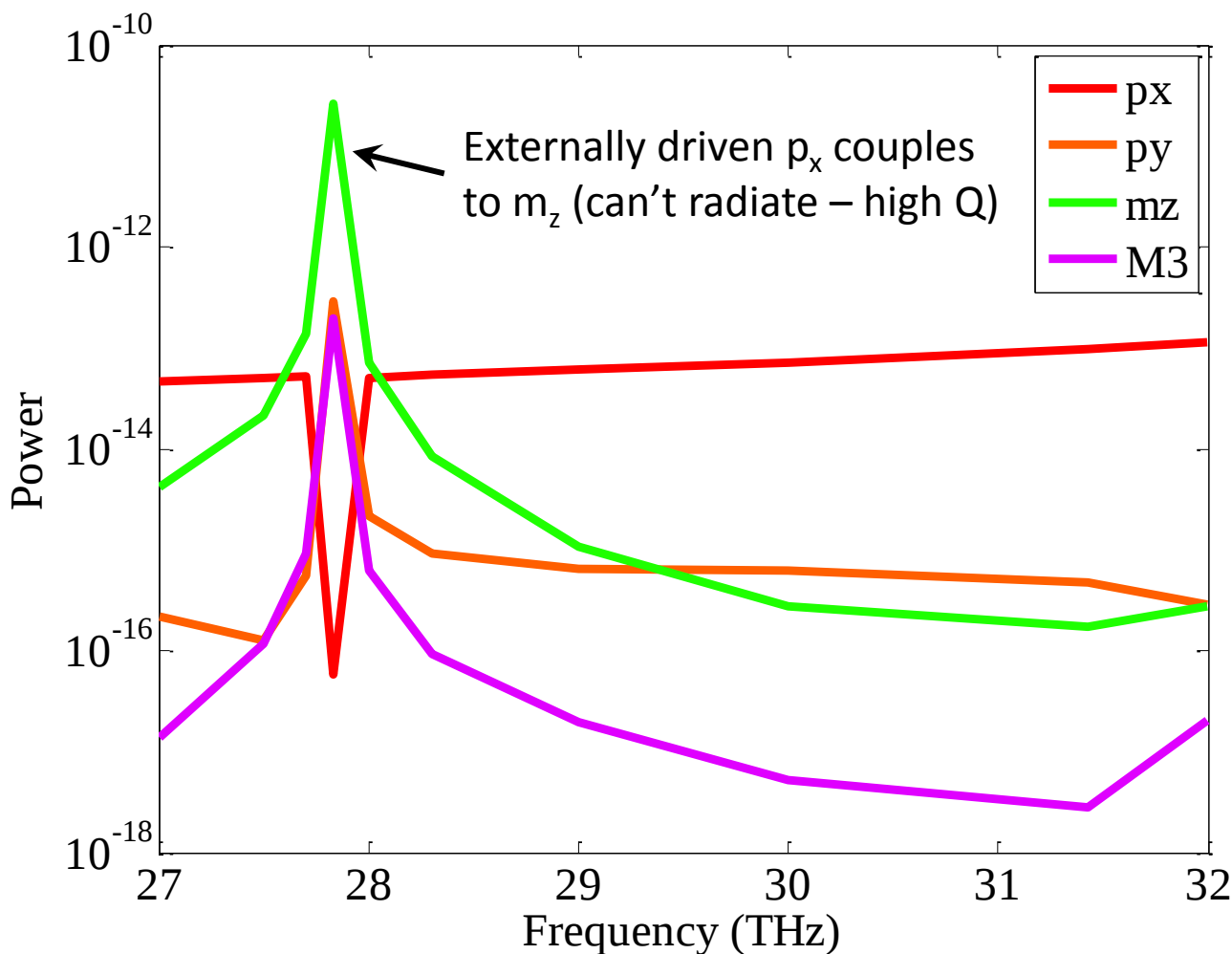
Understanding the nature of the Fano mode



Dr. Salvatore Campione

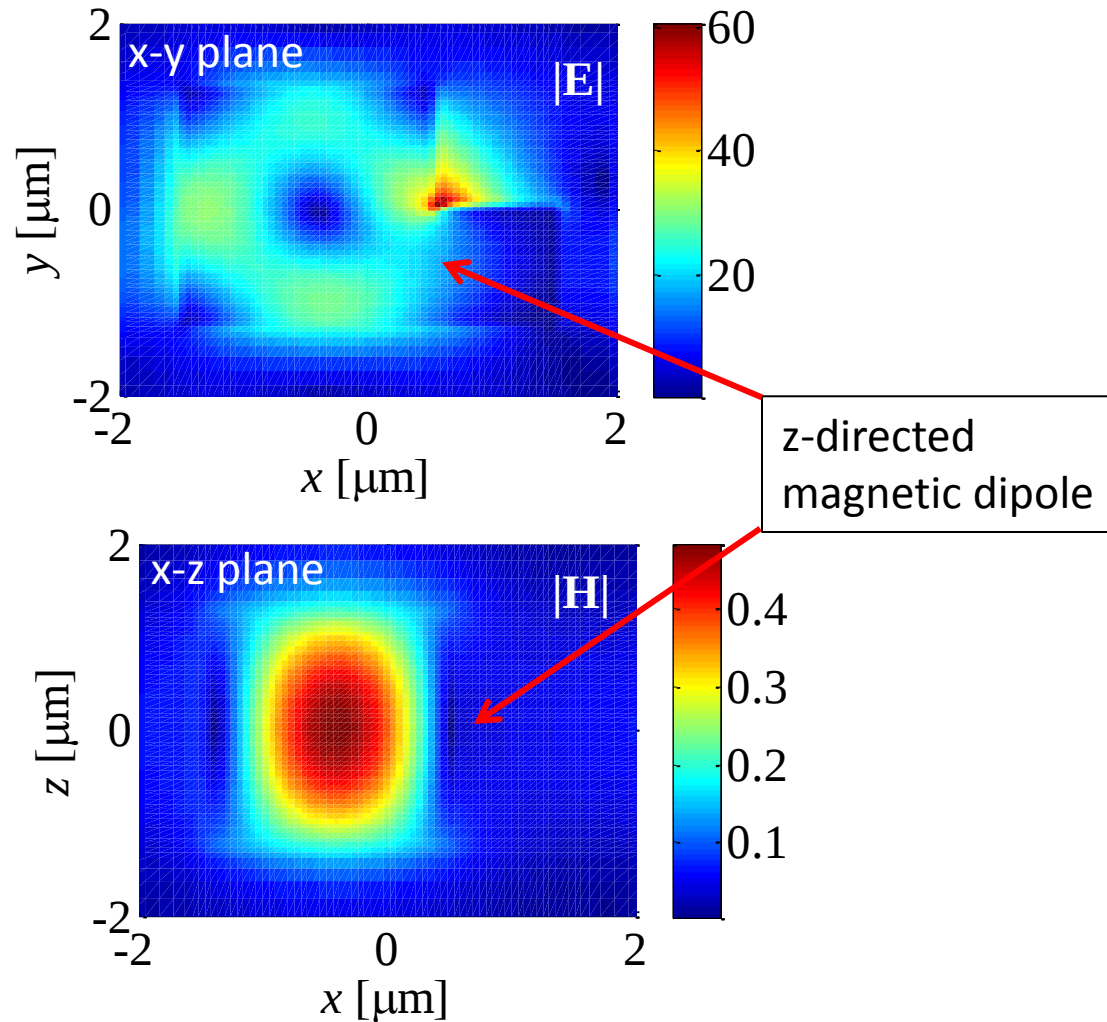
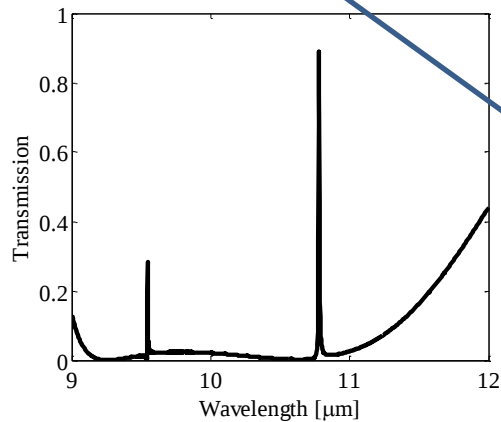
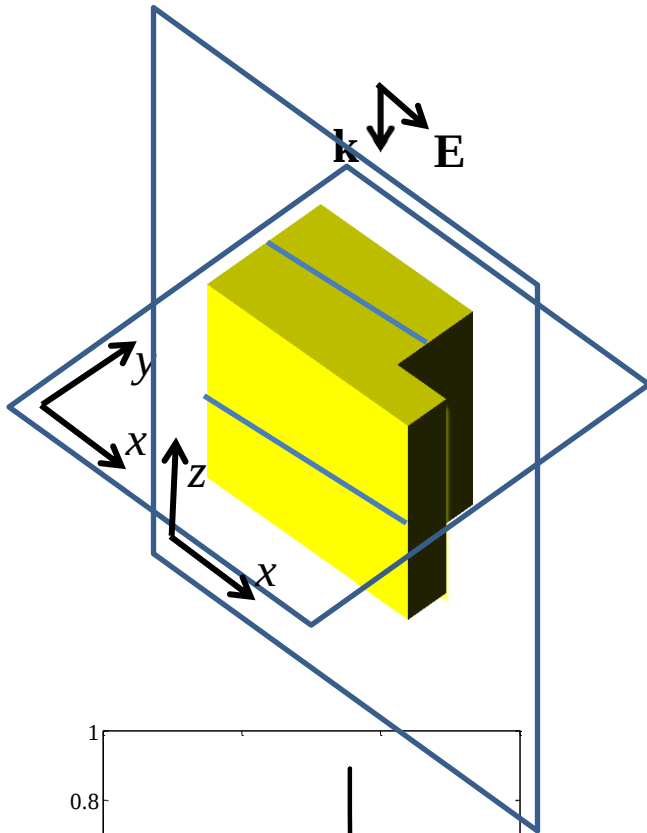
Multipole decomposition of resonator response

- Electric field excitation for full array
- Far-field scattering for single cube



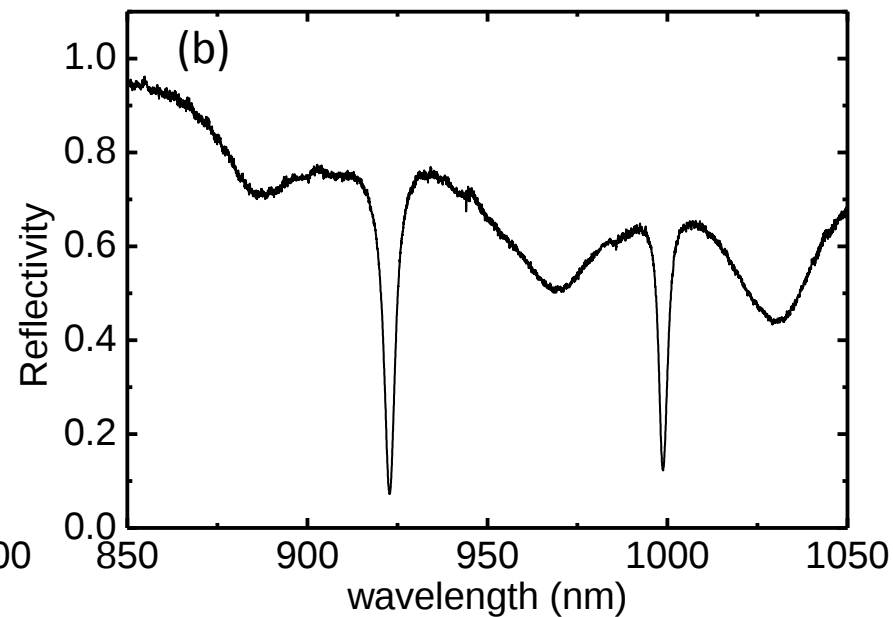
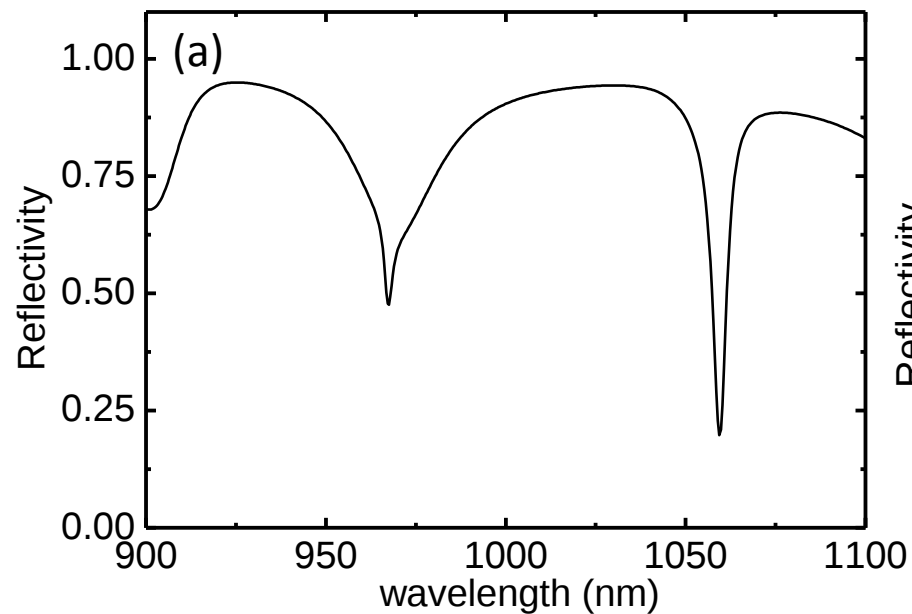
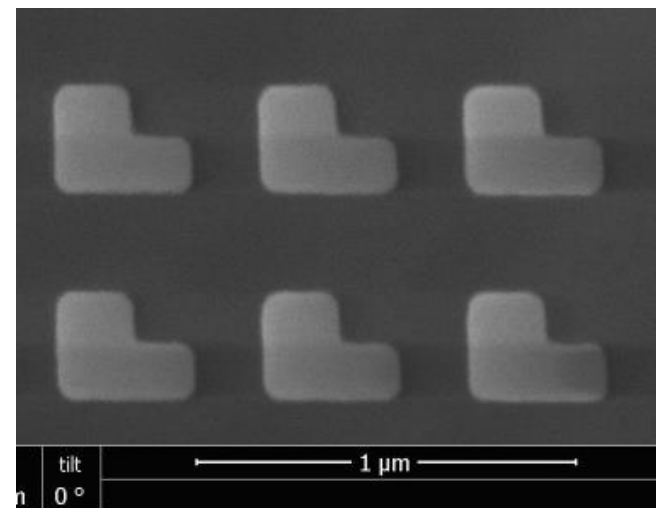
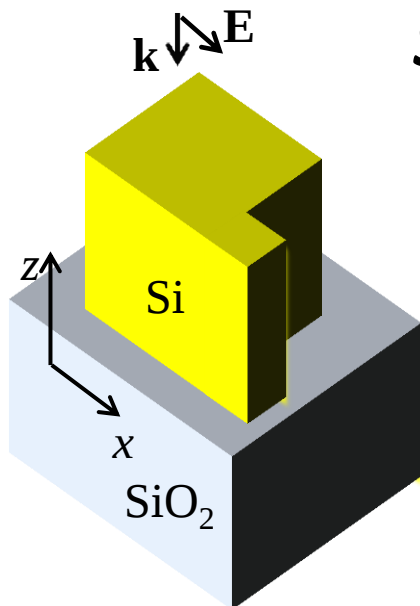
Resonant Mode Field Profiles

at the $\lambda = 10.8 \mu\text{m}$ resonance





Experimental verification: SOI Fano Resonators



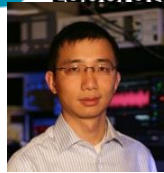


DRs are now possible in III-V semiconductors



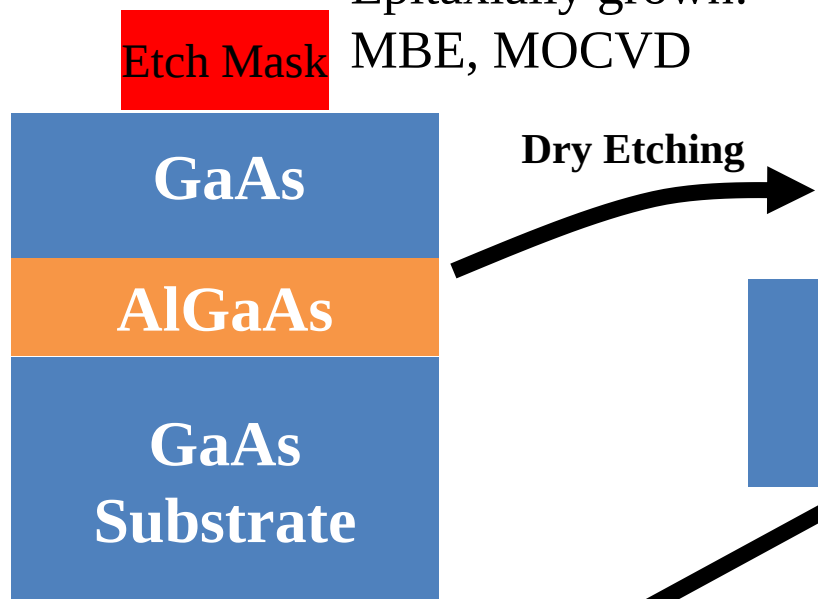
Sandia National Laboratories

New process for (Al)GaAs resonators

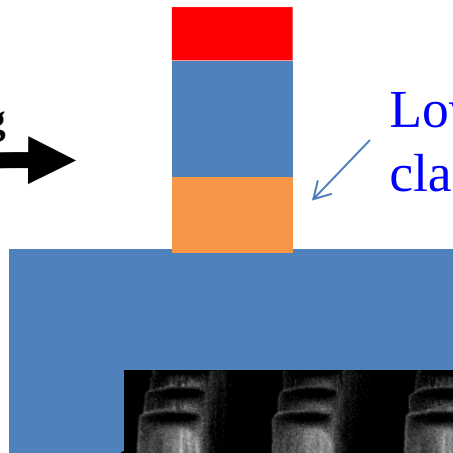


Sheng Liu

Epitaxially grown:
MBE, MOCVD

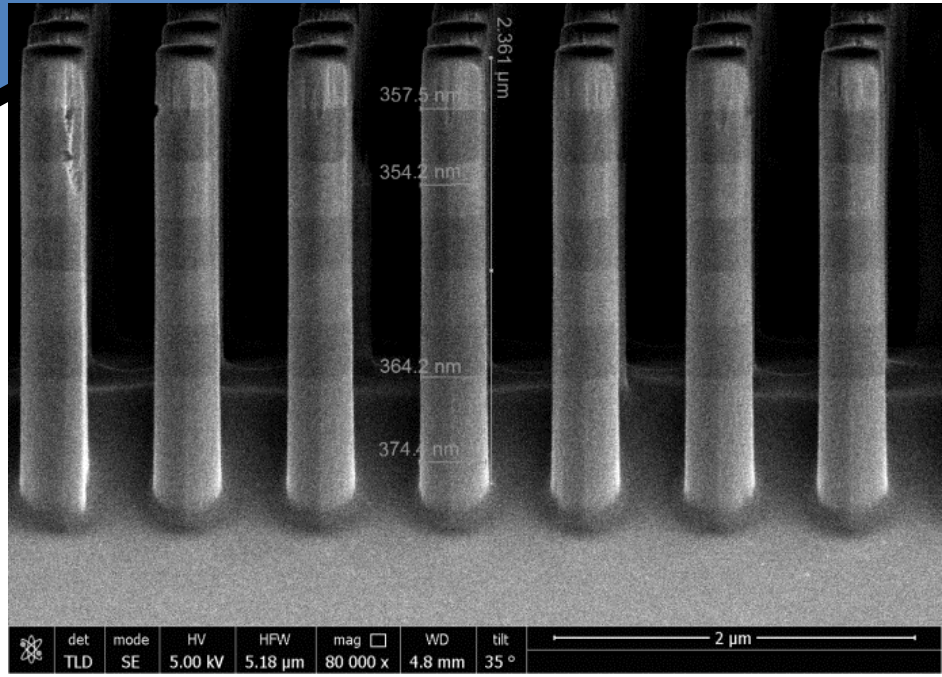
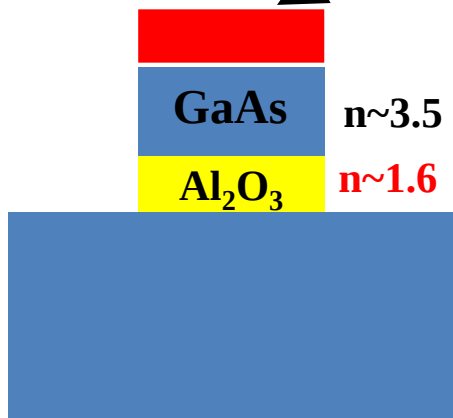


Dry Etching



Low refractive index cladding is needed!

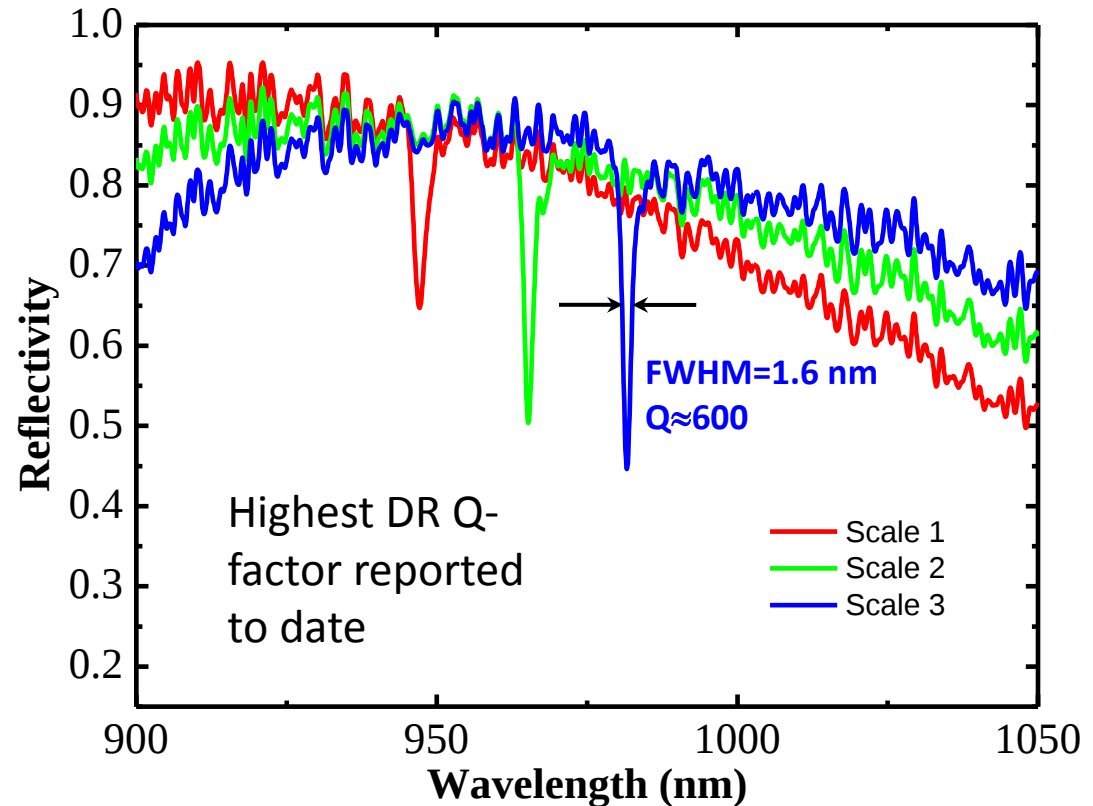
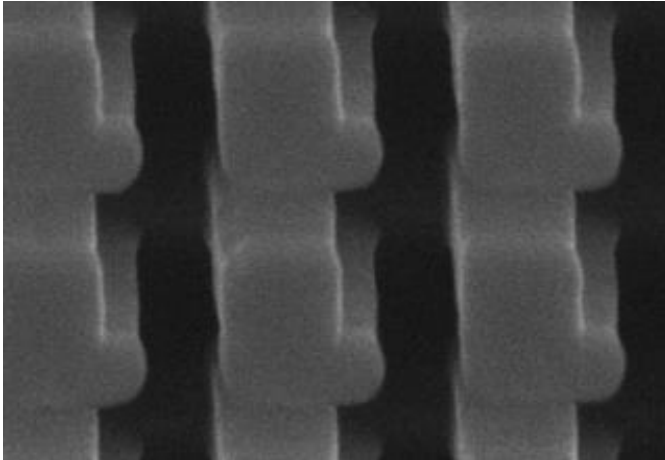
Oxidation



Sandia VCSEL: IEEE JSTQE, 3, 916 (1997)

GaAs Fano Resonators: $Q \approx 600$!

SEM of GaAs Fano resonators



- GaAs has a non-zero $\chi^{(2)} \rightarrow$ nonlinear devices (SHG, down-conversion, etc.)
- Can incorporate InGaAs quantum wells for gain and photon detection



Conclusions

- A new, simpler design for dielectric Fano resonators
 - One resonator per unit cell
- Inter-resonator coupling between bright and dark modes
 - Bright electric dipole and dark magnetic dipole
- Approach is scalable from NIR → RF
- High Q-factors for SOI (≈ 350) and GaAs (≈ 600)
- Extension to (Al)GaAs will allow for active devices
 - Spectrally selective detectors
 - Optical modulators
 - Nonlinear devices
 - Lasers??



END



Backup Slides



Multipolar expansion

The total far field can be decomposed to multipolar components as

$$\mathbf{E} = \mathbf{E}_{ED} + \mathbf{E}_{MD} + \mathbf{E}_{EQ} + \mathbf{E}_{MQ} + \mathbf{E}_{EO} + \mathbf{E}_{MO} + \dots$$

$$\mathbf{E}_{ED} = Z_0 \frac{ck^2}{4\pi} \frac{e^{ikr}}{r} \hat{\mathbf{r}} \times \mathbf{p} \times \hat{\mathbf{r}}$$

$$\mathbf{E}_{MD} = -Z_0 \frac{k^2}{4\pi} \frac{e^{ikr}}{r} \hat{\mathbf{r}} \times \mathbf{m}$$

$$\mathbf{E}_{EQ} = -Z_0 \frac{ick^3}{24\pi} \frac{e^{ikr}}{r} \hat{\mathbf{r}} \times \mathbf{Q}_{EQ} \times \hat{\mathbf{r}}$$

$$\mathbf{E}_{MQ} = Z_0 \frac{ik^3}{24\pi} \frac{e^{ikr}}{r} \hat{\mathbf{r}} \times \mathbf{Q}_{MQ}$$

$$\mathbf{E}_{EO} = -Z_0 \frac{ck^4}{24\pi} \frac{e^{ikr}}{r} \hat{\mathbf{r}} \times \mathbf{O}_{EO} \times \hat{\mathbf{r}}$$

$$\mathbf{E}_{MO} = Z_0 \frac{k^4}{24\pi} \frac{e^{ikr}}{r} \hat{\mathbf{r}} \times \mathbf{O}_{MO}$$

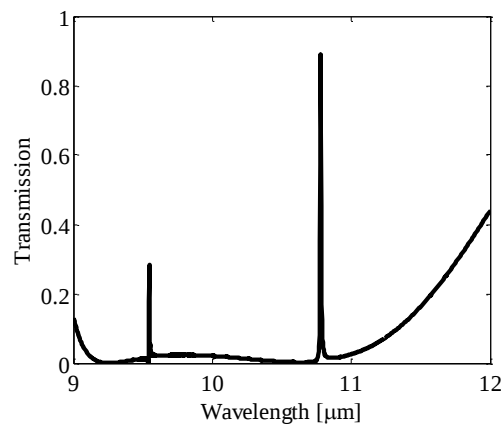
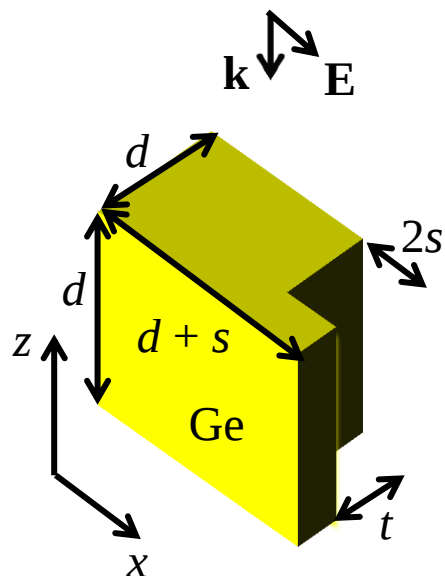
$$\text{Weight} = \frac{\int_0^{2\pi} \int_0^\pi \left(E_\theta^{FF} E_\theta^{\text{multipole}} + E_\phi^{FF} E_\phi^{\text{multipole}} \right) \sin\theta d\theta d\phi}{\text{Normalization factor} * \text{Coefficient in front of multipole above}}$$

$$P_i = \frac{1}{2Z_0} |E_i|^2 * \text{Normalization factor}$$

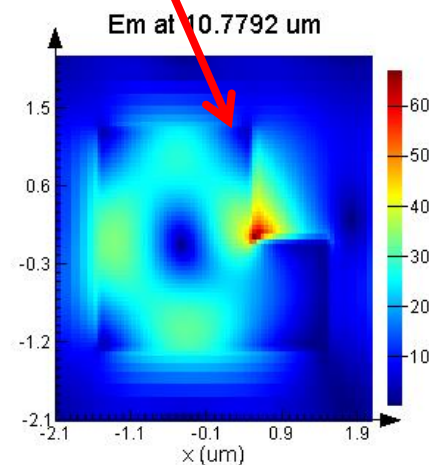
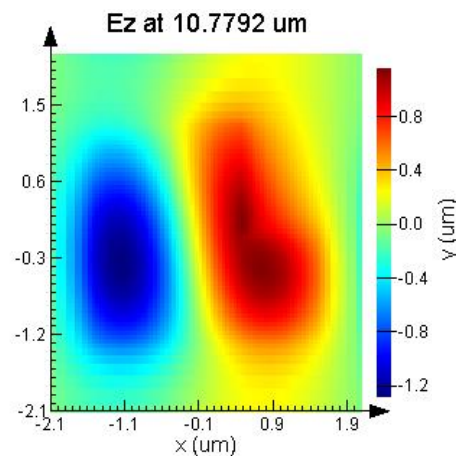
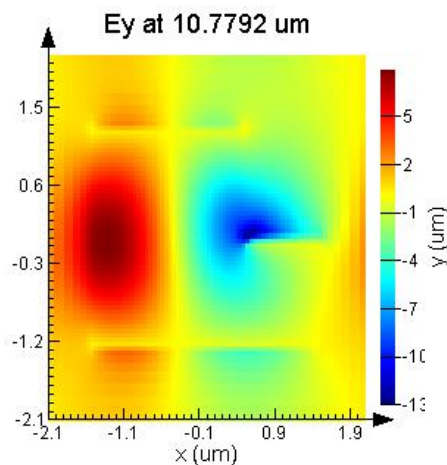
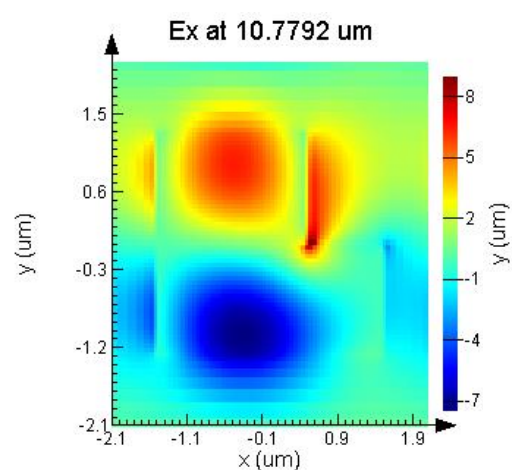
Expansion up to quadrupolar terms will be enough...

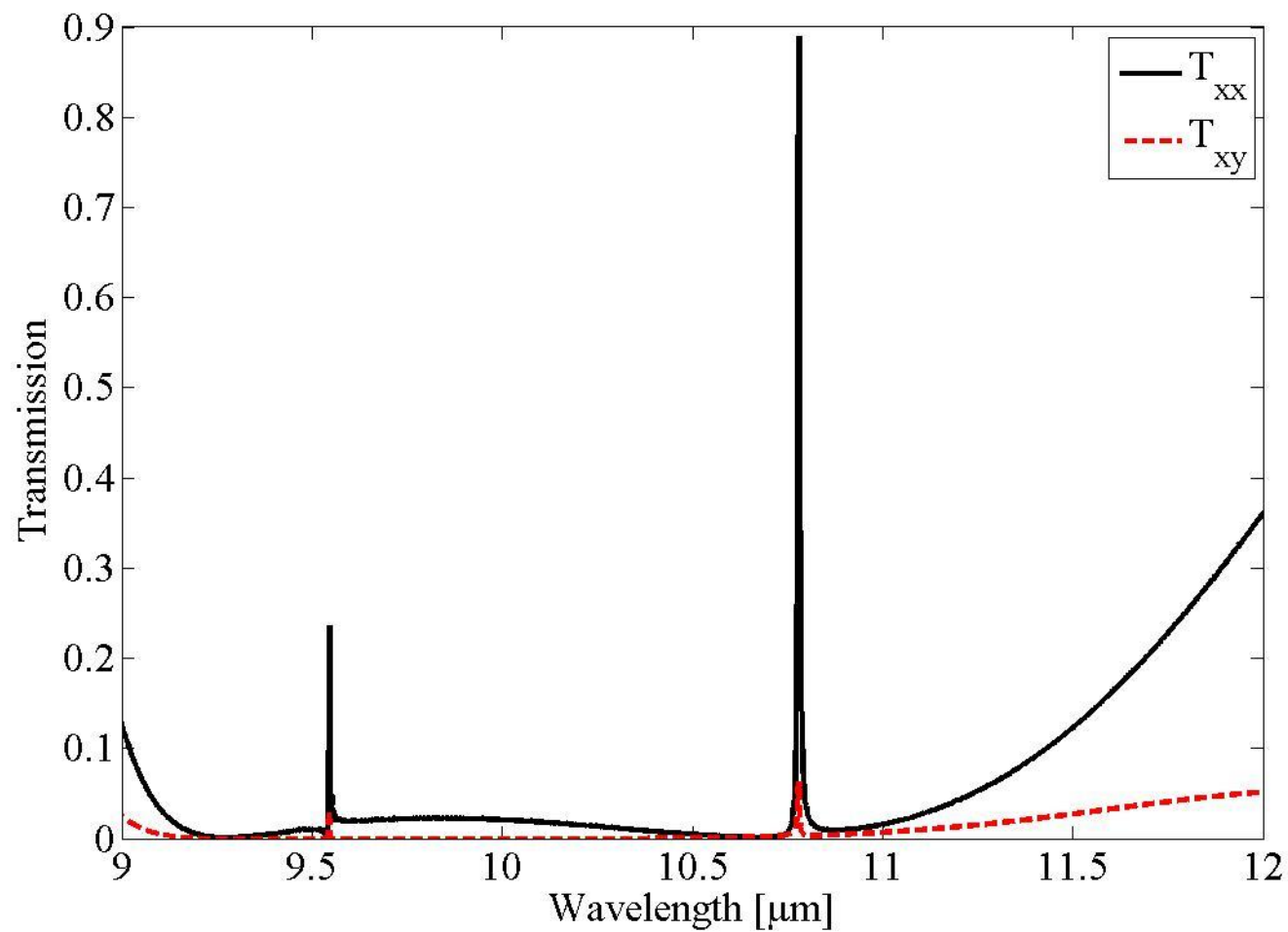


Top-L-cube – Electric field maps at Fano resonance 10.77 μm x-y plane



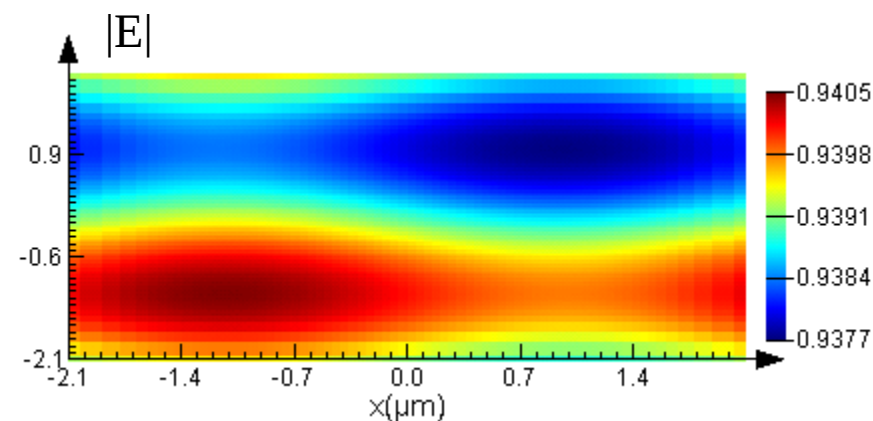
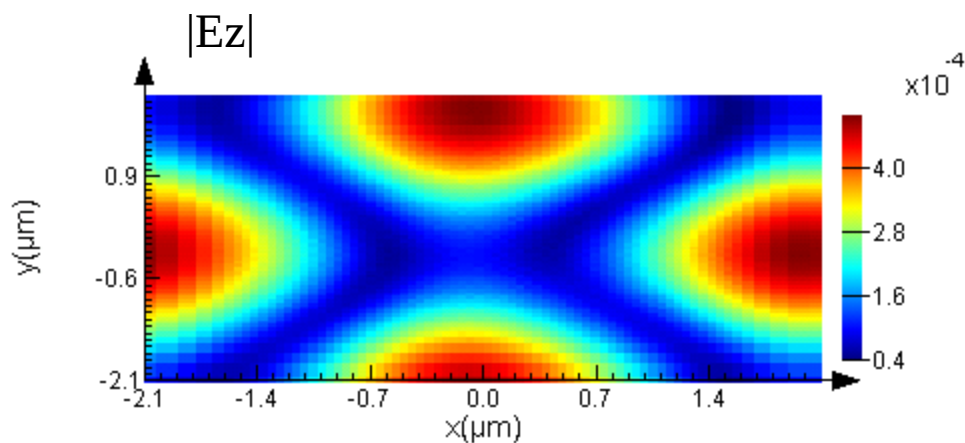
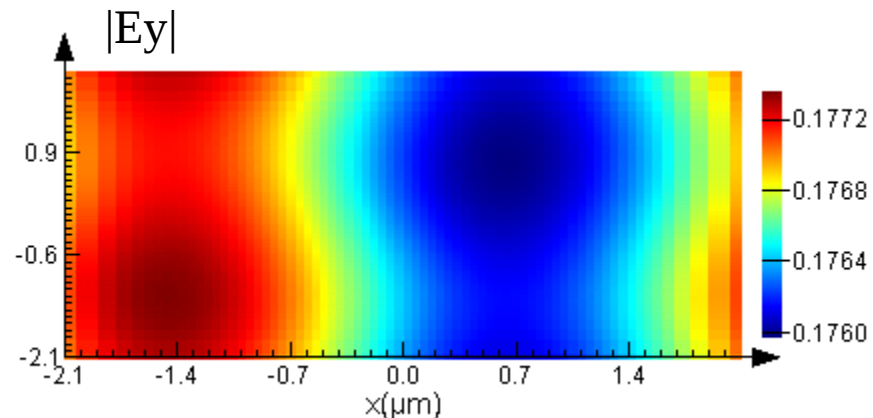
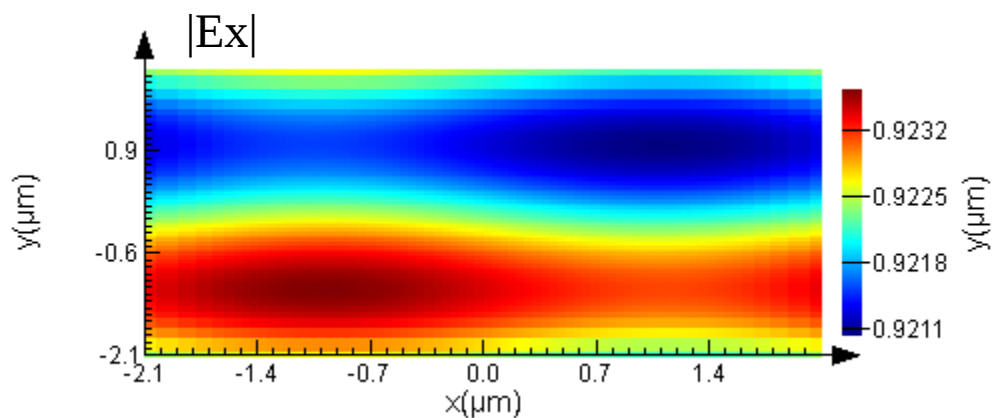
Magnetic dipole along z







Top-L-shape – Polarization at Fano resonance – E field at T monitor at 27.8314THz



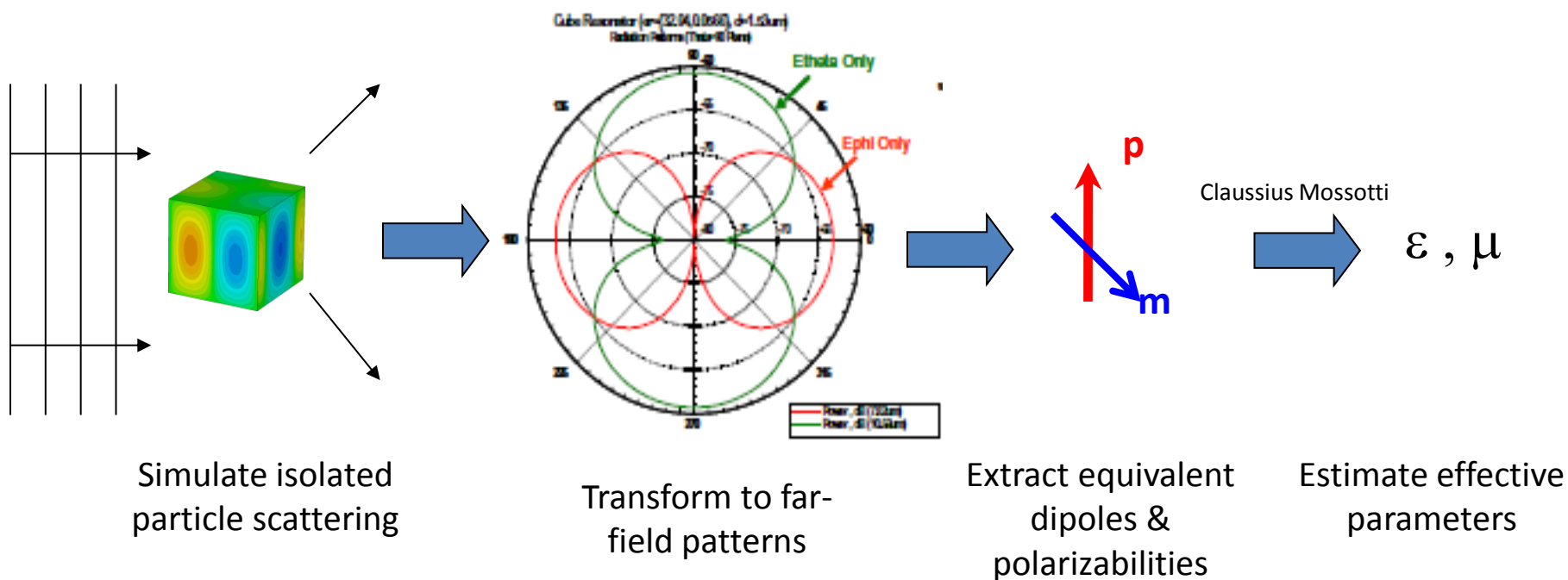


Extracting Resonator Polarizabilities: Isolated Particle Simulation and Moments (IPSaM)



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L. I. Bilio, et al., IEEE Antennas and Wireless Propagation Letters, 10, 1567, 2011
Rockstuhl, et al., PRB 83, 245119 (2011)



- fast, efficient, compatible with optimization
- general shapes: SRRs, dipoles, metals, DRs